

Bipolar PNP Bare Die – BTP6997

Part Description

The BTP6997 is a silicon BJT transistor available in bare die form and well suited for use in general purpose switching and amplifier applications. NPN complement is BTN6997.

Key Parameters:

- VCBO = -40V
- · VCEO = -40V
- VEBO = -6V
- hFE = 250- @ VCE = -2V, IC = -0.5A
- VCE(Sat) = -0.16V @ IC = -2A, IB = -200mA
- fT = 60 MHz @ VCE = -10V, IE = 0A
- COBO = 105pF @ VCB = -10V

Features

Very Low VCE(sat). Designed to provide performance equivalent to NXP / NEXPERIA PBSS5540Z

Die Size (Unsawn)

1640µm X 1640µm, 65 Mils X 65 Mils

This is a shortform datasheet only For the full datasheet

Please contact sales@siliconsupplies.com

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